Didier Goguenheim

List of Publications by Year
in descending order

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54	632	687363 13	610901 24
papers	citations	h-index	g-index

54	54	54	614
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Distance measurement using narrowband ZigBee devices. , 2014, , .		1
2	New technique to resolve carrier-phase cycle ambiguity for narrowband low-power systems. , 2014, , .		0
3	MOSFET layout modifications for hump effect removal. Microelectronic Engineering, 2013, 109, 168-171.	2.4	2
4	Different types of phase separation in binary monolayers of long chain alkyltrichlorosilanes on silicon oxide. RSC Advances, 2012, 2, 3014.	3.6	2
5	Dry and wet methods of silicon dioxide surface functionalisation with 3-aminopropyl trimethoxysilane: application to fullerene C<SUB align="right">60 anchoring. International Journal of Nanotechnology, 2012, 9, 312.	0.2	0
6	Portable microstimulator for chronic deep brain stimulation in freely moving rats. Journal of Neuroscience Methods, 2012, 209, 50-57.	2.5	36
7	Impact of chain length, temperature, and humidity on the growth of long alkyltrichlorosilane self-assembled monolayers. Physical Chemistry Chemical Physics, 2011, 13, 2870-2879.	2.8	39
8	Functionalization of Silicon Dioxide Surface with 3-Aminopropyltrimethoxysilane for Fullerene C₆₀ Immobilization. Journal of Nanoscience and Nanotechnology, 2011, 11, 9310-9315.	0.9	3
9	Off state incorporation into the 3 energy mode device lifetime modeling for advanced 40nm CMOS node. , 2010, , .		15
10	Influence of various process steps on the reliability of PMOSFETs submitted to negative bias temperature instabilities. Microelectronics Reliability, 2009, 49, 1008-1012.	1.7	12
11	Oxidation kinetics of Ni metallic films: Formation of NiO-based resistive switching structures. Thin Solid Films, 2008, 516, 4083-4092.	1.8	42
12	Assessment of temperature and voltage accelerating factors for 2.3â€"3.2nm SiO2 thin oxides stressed to hard breakdown. Microelectronics Reliability, 2008, 48, 335-341.	1.7	4
13	Dynamic stress method for accurate NVM oxide robustness evaluation for automotive applications. Microelectronics Reliability, 2008, 48, 1318-1321.	1.7	2
14	Geometry effects on the NBTI degradation of PMOS transistors. , 2008, , .		3
15	Total Recovery of Defects Generated by Negative Bias Temperature Instability (NBTI). , 2008, , .		2
16	Defects and relaxation during the negative bias temperature instability in PMOSFET. , 2008, , .		1
17	Advanced On-The-Fly Method with Correction of Initial Values to Characterize Negative Bias Temperature Instability Reliability. , 2008, , .		1
18	A comprehensive study of stress induced leakage current using a floating gate structure for direct applications in EEPROM memories. Microelectronics Reliability, 2007, 47, 1373-1377.	1.7	2

#	Article	IF	Citations
19	Impact of wafer charging on hot carrier reliability and optimization of latent damage detection methodology in advanced CMOS technologies. Microelectronics Reliability, 2005, 45, 487-492.	1.7	2
20	Experimental extraction of degradation parameters after constant voltage stress and substrate hot electron injection on ultrathin oxides. Microelectronics Reliability, 2005, 45, 883-886.	1.7	1
21	Impacts of the recovery phenomena on the worst-case of damage in DC/AC stressed ultra-thin NO gate-oxide MOSFETs. Microelectronics Reliability, 2005, 45, 1370-1375.	1.7	10
22	Degradation and recovery of polarization under synchrotron x rays in SrBi2Ta2O9 ferroelectric capacitors. Journal of Applied Physics, 2005, 97, 044106.	2.5	22
23	Ultrathin oxide reliability after combined constant voltage stress and substrate hot electron injection. Journal of Non-Crystalline Solids, 2005, 351, 1860-1865.	3.1	0
24	Deep hole trapping effects in the degradation mechanisms of 6.5â€"2 nm thick gate-oxide PMOSFETs. Microelectronic Engineering, 2004, 72, 106-111.	2.4	3
25	Hole injection enhanced hot-carrier degradation in PMOSFETs used for systems on chip applications with 6.5â€"2 nm thick gate-oxides. Microelectronics Reliability, 2004, 44, 65-77.	1.7	13
26	Carrier injection efficiency for the reliability study of 3.5â€"1.2 nm thick gate-oxide CMOS technologies. Microelectronics Reliability, 2003, 43, 1241-1246.	1.7	3
27	Efficiency of interface trap generation under hole injections in 2.1 nm thick gate-oxide P-MOSFETs. Journal of Non-Crystalline Solids, 2003, 322, 139-146.	3.1	3
28	Towards a full microscopic approach to the modeling of transistors with nanometer dimensions. Journal of Non-Crystalline Solids, 2003, 322, 160-167.	3.1	3
29	Comparison of degradation modes in 1.2â€"2.1 nm thick SiO2 oxides submitted to uniform and hot carrier injections in NMOSFETS. Journal of Non-Crystalline Solids, 2003, 322, 183-190.	3.1	7
30	Impact of carrier injection in 2.2 nm-thick SiO2 oxides after first and substrate enhanced electron injection. Journal of Non-Crystalline Solids, 2003, 322, 199-205.	3.1	5
31	Determination of the electrical properties of 2.5 nm thick silicon-based dielectric films: thermally grown SiOx. Journal of Non-Crystalline Solids, 2001, 280, 69-77.	3.1	3
32	Temperature and field dependence of stress induced leakage currents in very thin (<5 nm) gate oxides. Journal of Non-Crystalline Solids, 2001, 280, 78-85.	3.1	4
33	Hot-carrier reliability study of second and first impact ionization degradation in 0.15-Î¼m channel-length N-MOSFETS. Microelectronic Engineering, 2001, 59, 101-108.	2.4	5
34	Comparison of oxide leakage currents induced by ion implantation and high field electric stress. Solid-State Electronics, 2001, 45, 1355-1360.	1.4	9
35	Determination of the electrical properties of ultrathin silicon-based dielectric films: thermally grown SiNx. Solid-State Electronics, 2001, 45, 1265-1270.	1.4	5
36	Injection Mechanisms and Lifetime Prediction with the Substrate Voltage in 0.15Î¼m Channel-Length N-MOSFETs. Microelectronics Reliability, 2001, 41, 1313-1318.	1.7	10

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37	Comparison of oxide leakage currents induced by ion implantation and high field electric stress. Microelectronics Reliability, 2000, 40, 751-754.	1.7	4
38	Determination of the electrical properties of thermally grown ultrathin nitride films. Microelectronics Reliability, 2000, 40, 589-592.	1.7	2
39	Analysis of high temperature effects on performances and hot-carrier degradation in DC/AC stressed 0.35 Î¼m n-MOSFETs. Microelectronics Reliability, 1999, 39, 35-44.	1.7	18
40	Turn-around effects during dynamic operation in 0.25Î¼m CMOS technology from low to high temperature. Microelectronic Engineering, 1999, 48, 163-166.	2.4	2
41	Experimental study of the quasi-breakdown failure mechanism in 4.5 nm-thick SiO2 oxides. Microelectronics Reliability, 1999, 39, 165-169.	1.7	8
42	Stress induced leakage currents in N-MOSFETs submitted to channel hot carrier injections. Journal of Non-Crystalline Solids, 1999, 245, 41-47.	3.1	12
43	Hot-carrier injections in SiO2. Microelectronics Reliability, 1998, 38, 7-22.	1.7	17
44	HOT-CARRIER RELIABILITY IN n-MOSFETs USED AS PASS-TRANSISTORS. Microelectronics Reliability, 1998, 38, 539-544.	1.7	3
45	A coupled I(V) and charge-pumping analysis of Stress Induced Leakage Currents in 5nm-thick gate oxides. Microelectronic Engineering, 1997, 36, 141-144.	2.4	13
46	Influences of the different degradation mechanisms in AC-stressed p-MOSFET's during pass transistor operation. Microelectronic Engineering, 1997, 36, 305-308.	2.4	1
47	Comment on "hot-hole-induced negative oxide charges in n-MOSFETs" [with reply]. IEEE Transactions on Electron Devices, 1996, 43, 1473-1477.	3.0	5
48	Improved hot-carrier immunity of p-MOSFET's with 8nm thick nitrided gate-oxide during bi-directional stressing. Microelectronic Engineering, 1995, 28, 273-276.	2.4	2
49	Octadecyltrichlorosilane monolayers as ultrathin gate insulating films in metalâ€insulatorâ€semiconductor devices. Applied Physics Letters, 1993, 62, 2256-2258.	3.3	92
50	Theoretical calculation of the electron-capture cross section due to a dangling bond at the Si(111)-SiO2interface. Physical Review B, 1991, 44, 1724-1733.	3.2	37
51	Nature of the defects generated by electric field stress at the Siâ€SiO2interface. Applied Physics Letters, 1991, 58, 490-492.	3.3	22
52	New insights on the electronic properties of the trivalent silicon defects at oxidized ã€ˆ100ã€‰ silicon surfaces. Applied Physics Letters, 1990, 57, 1206-1208.	3.3	45
53	Theoretical and experimental aspects of the thermal dependence of electron capture coefficients. Journal of Applied Physics, 1990, 68, 1059-1069.	2.5	53
54	Accurate measurements of capture cross sections of semiconductor insulator interface states by a trapâ€filling experiment: The chargeâ€potential feedback effect. Journal of Applied Physics, 1990, 68, 1104-1113.	2.5	21